

/ Revised record

E	2016-5				
F	2020-4-27	1			
A	2021-12-17	all	BR Q 4R Q AEC-Q101 , Q 245±5°C 5±0.5sec 255±5°C 5± 0.5sec		

/ Descriptions

TO-252 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a TO-252 Plastic Package.

/ Features

饱和压降小， h_{FE} 高且线性好，符合 AEC-Q101 标准高可靠性要求，无卤产品。

Low saturation voltage, excellent h_{FE} linearity and high h_{FE} , Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

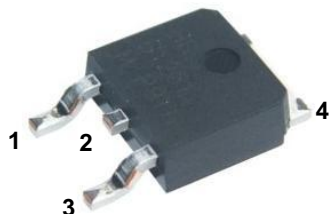
用于 3 瓦音频放大输出，电压调节器，电源转换和继电器驱动，满足汽车应用的严格要求。

Output stage of 3 watts audio amplifier, voltage regulator, DC-DC converter and relay driver, Meet the stringent requirements of automotive applications.

/ Equivalent Circuit



/ Pinning



PIN1 : Base

PIN 2,4 : Collector

PIN 3 : Emitter

/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	Q	P	E
h_{FE} Range	60~120	100~200	160~320	200~400

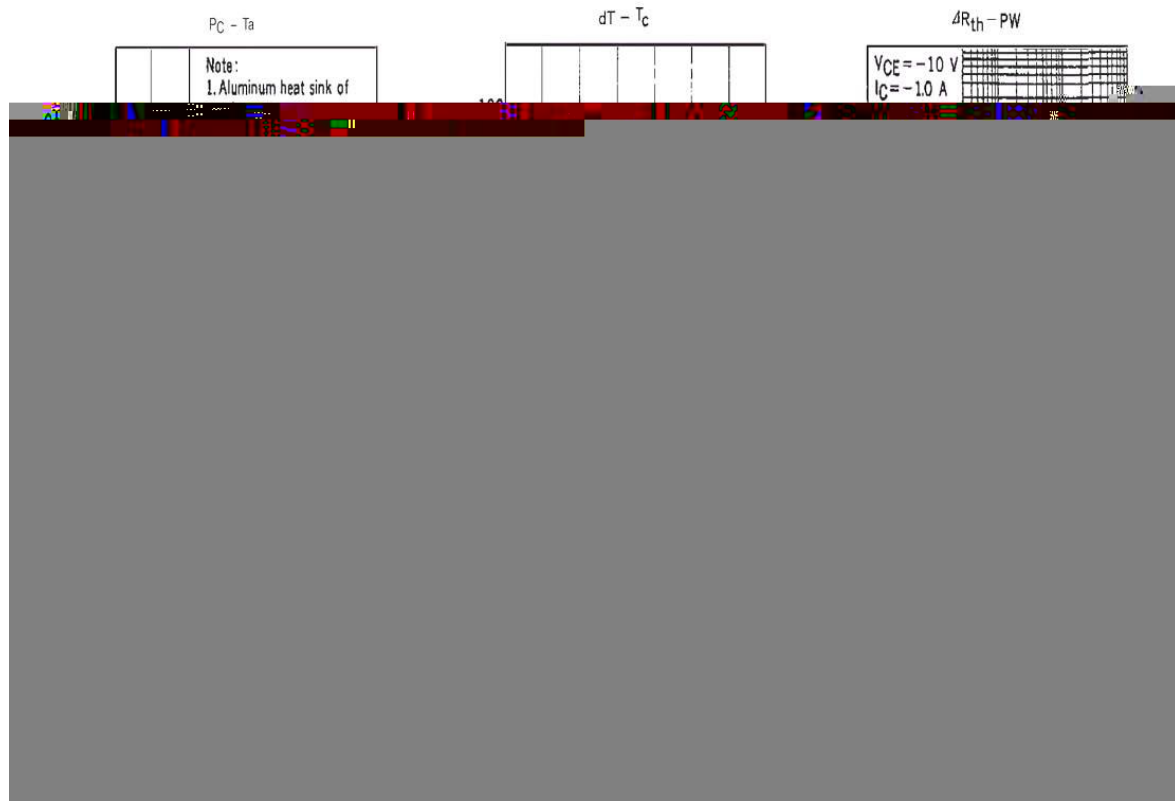
/ Absolute Maximum Ratings($T_a=25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-30	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Power Dissipation	P_C	1.0	W
	$P_C(T_C=25^\circ\text{C})$	10	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

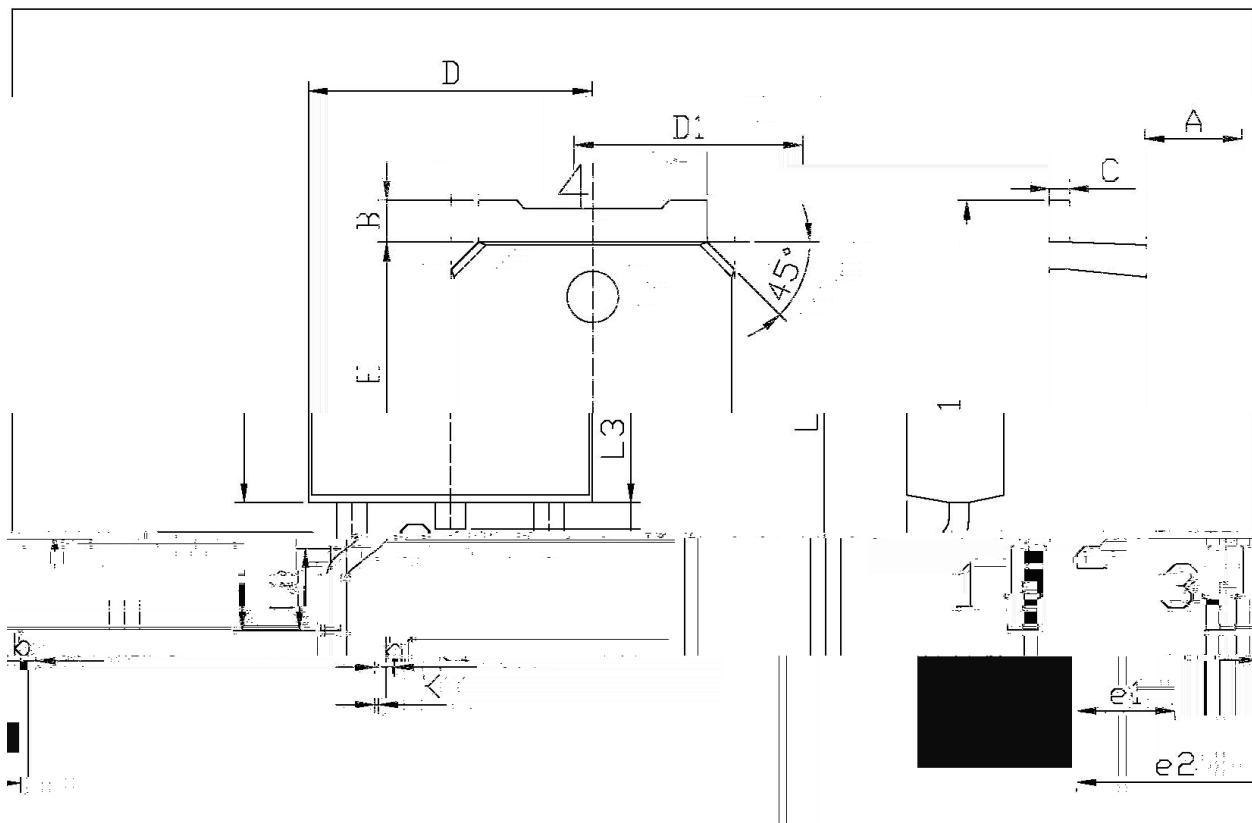
/ Electrical Characteristics($T_a=25^\circ\text{C}$)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-100\mu\text{A}$ $I_E=0$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1\text{mA}$ $I_B=0$	-30			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-10\mu\text{A}$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-30\text{V}$ $I_E=0$			-1.0	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-3.0\text{V}$ $I_C=0$			-1.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-2.0\text{V}$ $I_C=-1.0\text{A}$	60	160	400	
	$h_{FE(2)}$	$V_{CE}=-2.0\text{V}$ $I_C=-20\text{mA}$	30	220		
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2.0\text{A}$ $I_B=-0.2\text{A}$		-0.3	-0.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C=-2.0\text{A}$ $I_B=-0.2\text{A}$		-1.0	-2.0	V
Transition Frequency	f_T	$I_C=-1.0\text{A}$ $V_{CE}=-5.0\text{V}$		80		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}$ $I_E=0$ $f=1.0\text{MHz}$		55		pF

/ Electrical Characteristic Curve



/ Package Dimensions

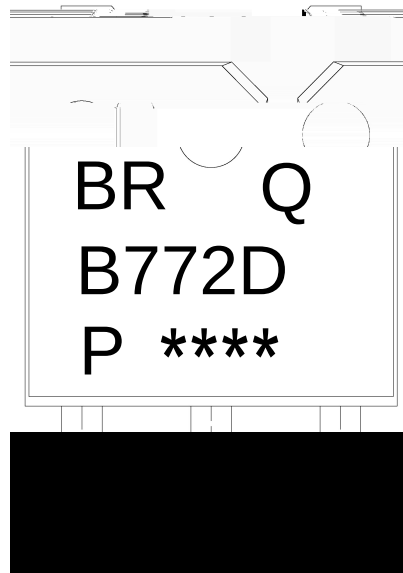


单位: mm

Dimensions in Millimeters		Dimensions in Millimeters			
Symbol	Min	Max	Symbol	Min	
Max					
6.35		3.20	3.40	6.35	
3.34		0.95	1.25	2.24	
4.73		0.70	0.90	4.43	
10.35		0.45	0.55	9.83	
2.50		0.40	0.50	2.00	
0.90		6.45	6.75	L3	0.60
0.10		5.10	5.50	K	0.00

TQ-252

/ Marking Instructions



BR

Q

B772D

P: h

Note:

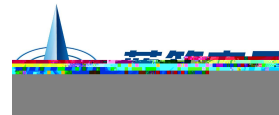
BR: Company Code

Q: Automobile halogen-free product Code

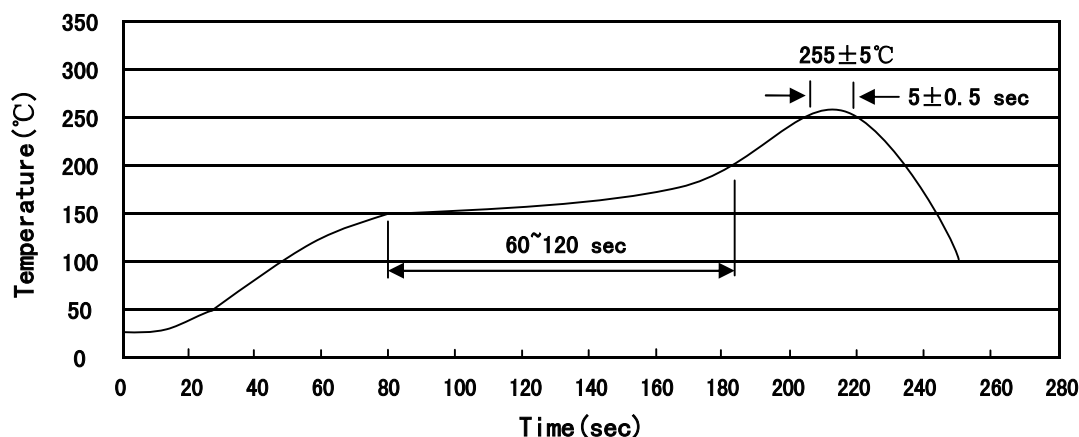
B772D: Product Type Code

P: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-----------|---------|--|
| 1 | 150 | 200 | 60 | 120sec; | 1.Preheating:150~200°C, Time:60~120sec. |
| 2 | 255±5 | | 5±0.5sec; | | 2.Peak Temp.:255±5°C, Duration:5±0.5sec. |
| 3 | | 2 | 10°C/sec. | | 3. Cooling Speed: 2~10°C/sec. |

/ Resistance to Soldering Heat Test Conditions

260±5°C

10±1 sec.

Temp.:260±5°C

Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-252	2,500	2	5,000	6	30,000	13" ×16	360×360×50	380×335×366

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-251/252	75	48	3,600	5	18,000	526×20.5×5.25	555×164×50	575×290×180

/ Notices